

#### **DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

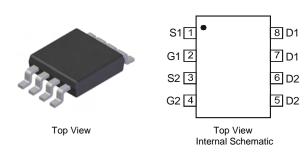
### **Features**

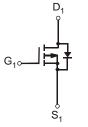
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

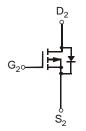
### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)

SO-8







P-Channel MOSFET

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# **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-20	V
Gate-Source Voltage			$V_{GSS}$	±12	V
Continuous Drain Current (Note 3) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 85°C	I <sub>D</sub>	-4.6 -3	А
Pulsed Drain Current (Note 4)			I <sub>DM</sub>	-20	Α

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P <sub>D</sub>	1.15	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C	R <sub>0JA</sub>	109	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 3. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 4. Repetitive rating, pulse width limited by junction temperature.

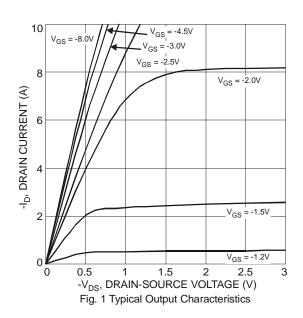


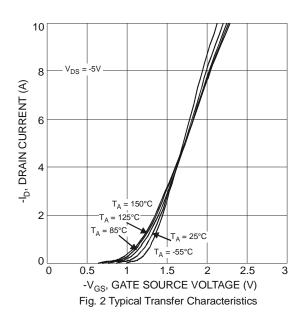
## Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	-	-	٧	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	-1.0	μΑ	$V_{DS} = -16V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	1	-	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(th)}$	-0.45	-	-1.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	P (-)	- 55 - 76	55	55 75	mΩ	$V_{GS} = -4.5V$ , $I_{D} = -4.8A$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)		76	110		$V_{GS} = -2.5V, I_D = -1A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	10	-	S	$V_{DS} = -9V, I_{D} = -3.4A$	
Diode Forward Voltage	$V_{SD}$	-	-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -2A$	
DYNAMIC CHARACTERISTICS (Note 6)						_	
Input Capacitance	Ciss	-	608.4	-	pF	\	
Output Capacitance	Coss	-	81.5	-	pF	$V_{DS} = -6V, V_{GS} = 0V$ - f = 1.0MHz	
Reverse Transfer Capacitance	$C_{rss}$	-	72.4	-	pF	1 = 1.000112	
Gate Resistance	$R_g$	-	44.91	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	$Q_g$	-	6.5	-	nC	$V_{DS} = -10V$ , $V_{GS} = -4.5V$ , $I_{D} = -3.2A$	
Gate-Source Charge	$Q_{gs}$	-	0.9	-	nC		
Gate-Drain Charge	$Q_{gd}$	-	1.5	-	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	12.45	-	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$ $R_{L} = 10\Omega, R_{G} = 1\Omega, I_{D} = -1A$	
Turn-On Rise Time	t <sub>r</sub>	-	10.29	-	ns		
Turn-Off Delay Time	t <sub>D(off)</sub>	-	46.52	-	ns		
Turn-Off Fall Time	t <sub>f</sub>	-	22.19	-	ns		

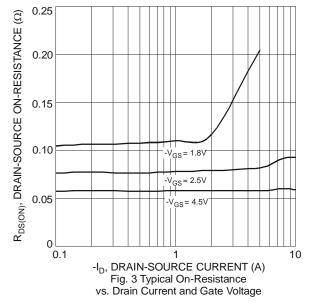
Notes:

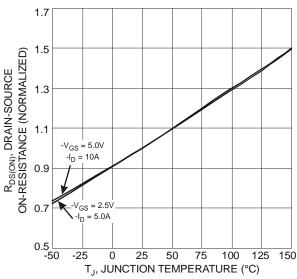
- 5. Short duration pulse test used to minimize self-heating effect.
- 6. Guaranteed by design. Not subject to production testing.

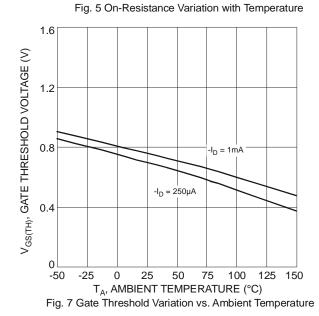












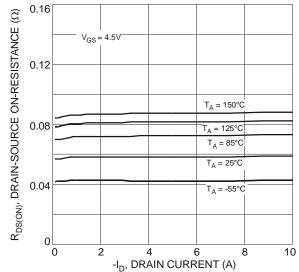


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

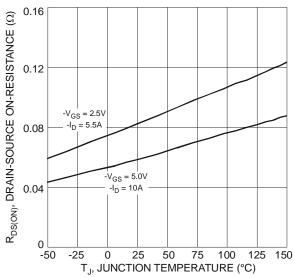


Fig. 6 On-Resistance Variation with Temperature

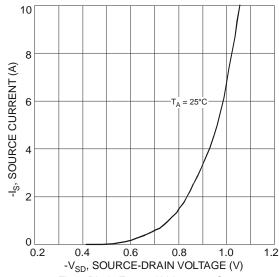
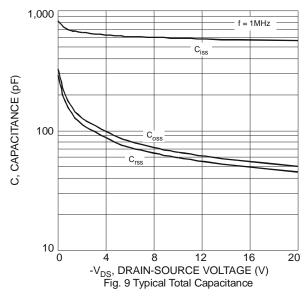


Fig. 8 Diode Forward Voltage vs. Current





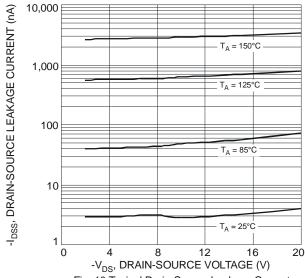
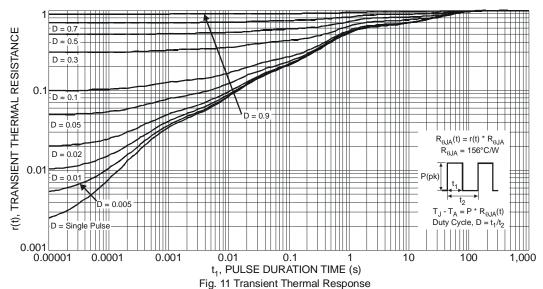


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

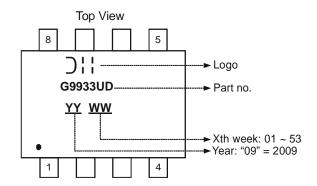


## Ordering Information (Note 7)

Part Number	Case	Packaging
DMG9933USD-13	SO-8	2500 / Tape & Reel

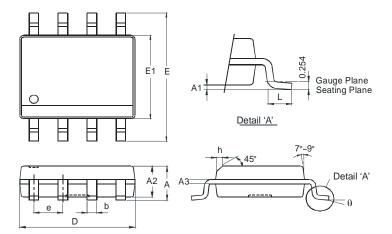
Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



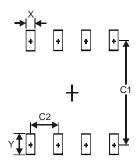


## **Package Outline Dimensions**



SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
E	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Х	0.60
Υ	1.55
C1	5.4
C2	1.27



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